

**AMENDMENTS TO THE CLAIMS**

1-16. (Canceled)

Please add the following new claims.

17. (New) A thin film semiconductor device comprising:

a gate electrode in contact with an insulating substrate;

a gate insulating film in contact with a gate electrode, said gate electrode being between said insulating substrate and said gate insulating film,

wherein a thickness of said gate insulating film is greater than a thickness of said gate electrode.

18. (New) The thin film semiconductor device according to claim 17, wherein a semiconductor thin film is in contact with said gate insulating film, said semiconductor thin film including a source region, a channel region, and a drain region.

19. (New) The thin film semiconductor device according to claim 18, further comprising:

a stopper is in contact with said channel region, said channel region being between said gate insulating film and said stopper.

20. (New) The thin film semiconductor device according to claim 19, wherein said stopper is an insulator.

21. (New) The thin film semiconductor device according to claim 19, wherein said source and drain regions are adjacent said channel region.

22. (New) The thin film semiconductor device according to claim 18, wherein said gate electrode includes a lower layer and an upper layer, said lower layer being between said insulating substrate and said upper layer.

23. (New) The thin film semiconductor device according to claim 22, wherein said lower layer is in contact with said insulating substrate.

24. (New) The thin film semiconductor device according to claim 22, wherein said upper layer is in contact with said lower layer.

25. (New) The thin film semiconductor device according to claim 22, wherein said gate insulating film is between said upper layer and said semiconductor thin film.

26. (New) The thin film semiconductor device according to claim 22, wherein an electric resistance of said upper layer is greater than said lower layer, heat conductivity of said lower layer being greater than said upper layer.

27. (New) The thin film semiconductor device according to claim 22, wherein said lower layer is a metallic material and said upper layer is another metallic material.

28. (New) The thin film semiconductor device according to claim 27, wherein said metallic material contains aluminum.

29. (New) The thin film semiconductor device according to claim 28, wherein said metallic material is aluminum.

30. (New) The thin film semiconductor device according to claim 28, wherein said metallic material is an alloy of aluminum and silicon.

31. (New) The thin film semiconductor device according to claim 27, wherein said another metallic material is from the group consisting of molybdenum, tantalum, tungsten and chromium.

32. (New) The thin film semiconductor device according to claim 31, wherein said another metallic material is molybdenum.

33. (New) The thin film semiconductor device according to claim 31, wherein said another metallic material is tantalum.

34. (New) The thin film semiconductor device according to claim 31, wherein said another metallic material is tungsten.

35. (New) The thin film semiconductor device according to claim 31, wherein said another metallic material is chromium.

36. (New) A display device comprising:

a plurality of pixels arranged in a matrix form, one of said plurality of pixels being driven by the thin film semiconductor device according to claim 18.